

IN THE CLAIMS:

Please amend claims 1, 5, 8 and 9 by rewriting these claims as follows:

Sub D1
C1 -- 1. (Twice amended) A semiconductor wafer having an outer peripheral face containing a notch, an inner wall face of the notch containing markings with history information concerning fabrication steps used to fabricate the semiconductor wafer, which markings can be read after fabrication of the semiconductor wafer is completed, and the markings being made from dot marks respectively having a maximum length of 1 to 13 μm . --

Sub D4
C2 -- 5. (Twice amended) The semiconductor wafer according to Claim 2, wherein the dot marks are formed on either one of the upper and lower inclined faces. --

Sub D6
C3 -- 8. (Amended) The semiconductor wafer according to Claim 1, wherein the dot marks are formed by irradiating a laser beam. --

-- 9. (Twice amended) The semiconductor wafer according to Claim 1, wherein the dot marks have a height in the range of 0.005 to 5 μm . --